

Features

- Any frequency between 220.000001 MHz and 700 MHz accurate to 6 decimal places
- LVPECL, LVDS and HCSL output signaling types
- 0.1ps RMS phase jitter (random) for Ethernet applications
- Frequency stability as low as ±10 ppm
- Wide temperature range from -40°C to 85°C
 Contact SiTime for higher temperature range options
- Industry-standard packages: 3.2x2.5, 7.0x5.0 mm Contact SiTime for 5.0 x 3.2 mm package

Applications

- 10/40GB Ethernet, SONET, SATA, SAS, Fibre Channel
- Telecom, networking, instrumentation, storage, servers







Electrical Characteristics

All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage

Table 1. Electrical Characteristics - Common to LVPECL, LVDS and HCSL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition			
	Frequency Range								
Output Frequency Range	f	220.000001	-	700	MHz	Accurate to 6 decimal places			
	Frequency Stability								
		-10	-	+10	ppm				
Frequency Stability	F_stab	-20	_	+20	ppm	Inclusive of initial tolerance, operating temperature, rated power			
Frequency Stability	i _stab	-25	_	+25	ppm	supply voltage and load variations			
		-50	_	+50	ppm				
First Year Aging	F_aging1	_	±1	_	ppm	At 25°C			
			Te	emperature l	Range				
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial			
Operating reinperature Kange	1_036	-40	_	+85	°C	Industrial. Contact SiTime for higher temperature range options			
				Supply Volt	age				
	Vdd	2.97	3.3	3.63	V				
		2.7	3.0	3.3	V				
Supply Voltage		2.52	2.8	3.08	V				
		2.25	2.5	2.75	V				
		1	Inc	out Characte	eristics				
Input Voltage High	VIH	70%		_	Vdd	Pin 1, OE			
Input Voltage Low	VIL	_	_	30%	Vdd	Pin 1, OE			
Input Pull-up Impedance	Z_in	-	100	-	kΩ	Pin 1, OE logic high or logic low			
			Ou	tput Charac	teristics				
Duty Cycle	DC	45	_	55	%				
			Sta	rtup and OE	Timing				
Start-up Time	T_start	-	_	5	ms	Measured from the time Vdd reaches its rated minimum value.			
OE Enable/Disable Time	T_oe	-	-	510	ns	f = 322.265652 MHz - For other frequencies, T_oe = 500ns + 3 period			



Table 2. Electrical Characteristics - LVPECL Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Current Consumption							
Current Consumption	ldd	-	ı	84	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	-	1	55	mA	OE = Low	
Output Disable Leakage Current	l_leak	-	0.15	-	μΑ	OE = Low	
Maximum Output Current	I_driver	-	ı	30	mA	Maximum average current drawn from OUT+ or OUT-	
Output Characteristics							
Output High Voltage	VOH	Vdd-1.1	ı	Vdd-0.7	٧	See Figure 2	
Output Low Voltage	VOL	Vdd-1.9	ı	Vdd-1.5	٧	See Figure 2	
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	٧	See Figure 3	
Rise/Fall Time	Tr, Tf	-	250	-	ps	20% to 80%, see Figure 2	
				Jit	ter		
RMS Period Jitter ^[1]	T_jitt	-	1	2	ps	f = 322.265625 MHz, VDD = 3.3V or 2.5V	
RMS Phase Jitter (random)	T nhi	_	0.23	-	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds	
	T_phj	_	0.1	-	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, all Vdds	

Notes:

Table 3. Electrical Characteristics – LVDS Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Current Consumption							
Current Consumption	ldd	ı	_	76	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	-	-	55	mA	OE = Low	
Output Disable Leakage Current	I_leak	-	0.15	-	μΑ	OE = Low	
Output Characteristics							
Differential Output Voltage	VOD	250	_	450	mV	See Figure 4	
VOD Magnitude Change	ΔVOD	ı	-	50	mV	See Figure 4	
Offset Voltage	VOS	1.125	-	1.375	V	See Figure 4	
VOS Magnitude Change	ΔVOS	ı	-	50	mV	See Figure 4	
Rise/Fall Time	Tr, Tf	I	340	ı	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 4	
				Jit	ter		
RMS Period Jitter ^[2]	T_jitt	ì	1	2	ps	f = 322.265625 MHz, VDD = 3.3V or 2.5V	
DMC Dhoop litter (rendem)	Tabi		0.23	-	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds	
RMS Phase Jitter (random)	T_phj		0.1	-	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, all Vdds	

Notes:

2. Measured according to JESD65B

^{1.} Measured according to JESD65B

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220 to 700 MHz Ultra-low Jitter Differential Oscillator



Table 4. Electrical Characteristics – HCSL Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition		
	Current Consumption							
Current Consumption	ldd	_	_	84	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V		
OE Disable Supply Current	I_OE	ı	-	55	mA	OE = Low		
Output Disable Leakage Current	l_leak	-	0.15	-	μΑ	OE = Low		
Output Characteristics								
Output High Voltage	VOH	0.6	-	0.8	V	See Figure 2		
Output Low Voltage	VOL	-0.05	-	0.05	V	See Figure 2		
Output Differential Voltage Swing	V_Swing	1	1.4	1.8	V	See Figure 3		
Rise/Fall Time	Tr, Tf	-	350	-	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 2		
				Jitt	er			
RMS Period Jitter ^[3]	T_jitt	-	1	2	ps	f = 322.265625 MHz, VDD = 3.3V or 2.5V		
RMS Phase Jitter (random)	T_phj	-	0.23	_	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds		
		-	0.1	_	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, all Vdds		

Notes:

3. Measured according to JESD65B

Table 5. Pin Description

Pin	Мар	Functionality					
05410		Output Enable (OE)	H ^[4] : specified frequency output L: output is high impedance				
1			H or L or Open: No effect on output frequency or other device functions				
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation				
3	GND	Power	VDD Power Supply Ground				
4	OUT+	Output	Oscillator output				
5	OUT-	Output	Complementary oscillator output				
6	VDD	Power	Power supply voltage ^[5]				

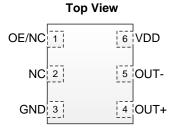


Figure 1. Pin Assignments

Notes:

- 4. In OE mode, a pull-up resistor of 10 k Ω or less is recommended if pin 1 is not externally driven.
- 5. A capacitor of value 0.1 μ F or higher between Vdd and GND is required. An additional 10 pF capacitor between Vdd and GND is required for the best phase jitter performance

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Table 6. Absolute Maximum

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge (HBM)	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C

Table 7. Thermal Consideration^[6]

Package	θJA, 4 Layer Board (°C/W)	θJC, Bottom (°C/W)
3225, 6-pin	TBD	TBD
7050, 6-pin	TBD	TBD

Notes:

Table 8. Maximum Operating Junction Temperature[7]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	80
85°C	95

Notes:

7. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 9. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C

^{6.} Refer to JESD51 for θ JA and θ JC definitions, and reference layout used to determine the θ JA and θ JC values in the above table.



Waveform Diagrams

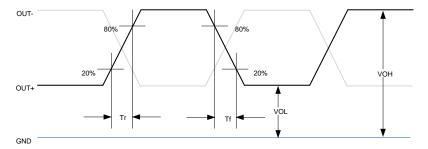


Figure 2. LVPECL/HCSL Voltage Levels per Differential Pin (OUT+/OUT-)

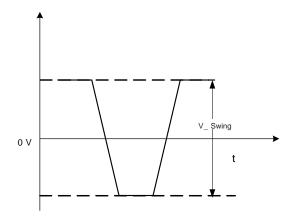


Figure 3. LVPECL/HCSL Voltage Levels across Differential Pair

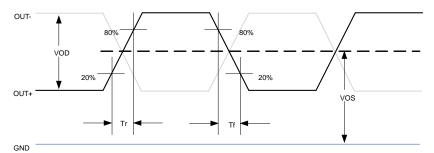


Figure 4. LVDS Voltage Levels per Differential Pin (OUT+/OUT-)



Termination Diagrams

LVPECL:

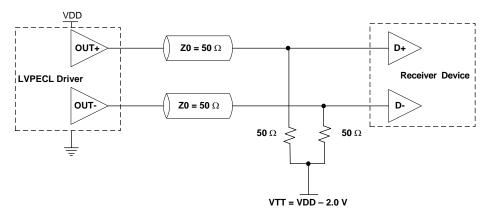


Figure 5. LVPECL Typical Termination

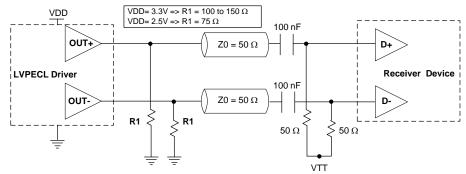


Figure 6. LVPECL AC Coupled Termination

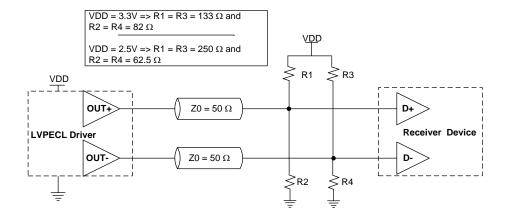


Figure 7. LVPECL with Thevenin Typical Termination



Termination Diagrams (Continued)

LVDS:

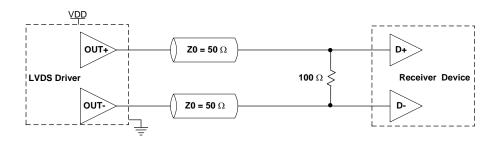


Figure 8. LVDS Single Termination (Load Terminated)

HCSL:

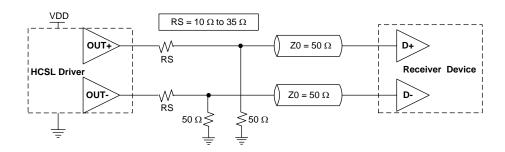
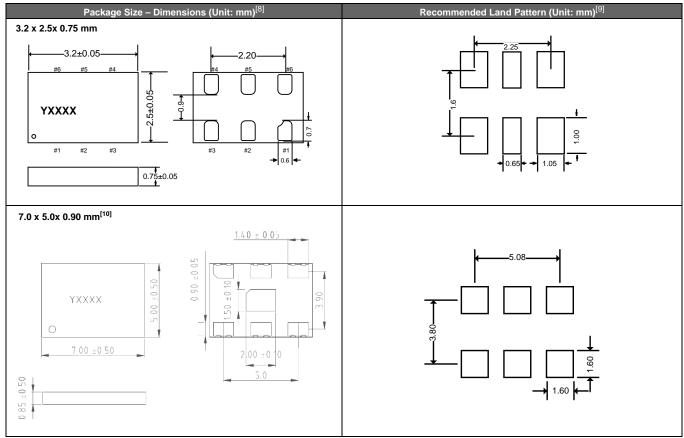


Figure 9. HCSL Typical Termination



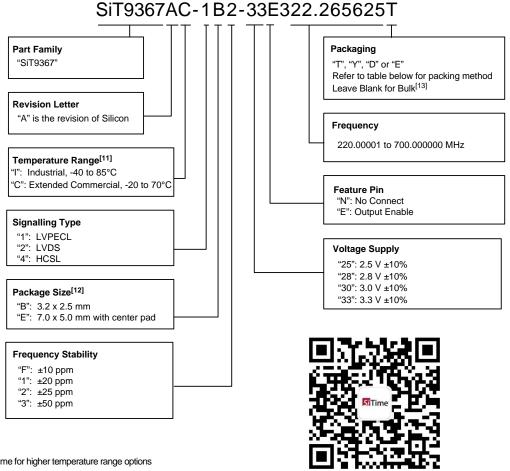
Dimensions and Patterns



- 8. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device. A capacitor of value 0.1 μF or higher between Vdd and GND is required.
 The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.



Ordering Information



Notes:

- 11. Contact SiTime for higher temperature range options
- 12. Contact SiTime for 5.0 x 3.2 package
- 13. Bulk is available for sampling only

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Table 10. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	_	_	_	_	Т	Υ
3.2 x 2.5	D	E	Т	Υ	_	_

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Table 11 . Revision History

Revision	Release Date	Change Summary
0.1	06/29/16	Initial draft
0.2	08/02/16	Revised T_jitt and T_phj values in electrical characteristics tables
0.21	08/25/16	Removed 5.0 x 3.2 mm package Revised the 12k -20 MHz phase jitter value
0.25	09/21/16	Revised the Electrical characteristics tables Revised 7050 package dimension

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